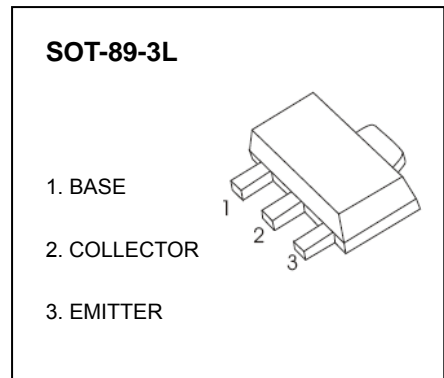


TRANSISTOR (NPN)

FEATURES

- Low Collector-Emitter Saturation Voltage
- Large Collector Power Dissipation and Current
- Mini Power Type Package



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	40	V
V_{CE0}	Collector-Emitter Voltage	20	V
V_{EB0}	Emitter-Base Voltage	7	V
I_C	Collector Current	5	A
P_C	Collector Power Dissipation	750	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	167	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=10\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=1\text{mA}$		200		
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=500\text{mA}$	230		800	
	$h_{FE(3)}$	$V_{CE}=2\text{V}, I_C=2\text{A}$	150			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3\text{A}, I_B=0.1\text{A}$			1	V
Transition frequency	f_T	$V_{CE}=6\text{V}, I_C=50\text{mA}, f=200\text{MHz}$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=1\text{MHz}$			50	pF

CLASSIFICATION OF $h_{FE(2)}$

RANK	Q	R	S
RANGE	230 - 380	340 - 600	560 - 800